



# 600 V IL420 800 V IL4208 Triac Optocoupler

## FEATURES

- High Input Sensitivity  $I_{FT}=2.0$  mA
- 600/800 V Blocking Voltage
- 300 mA On-State Current
- High Static dv/dt 10 kV/ $\mu$ s
- Inverse Parallel SCRs Provide Commutating dv/dt >10 kV/ $\mu$ s
- Very Low Leakage <10  $\mu$ A
- Isolation Test Voltage from Double Molded Package 5300 V<sub>RMS</sub>
- Small 6-Pin DIP Package
- Underwriters Lab File #E52744
- VDE Approval #0884 Available with Option 1

## Maximum Ratings

### Emitter

Reverse Voltage .....	6.0 V
Forward Current .....	60 mA
Surge Current .....	2.5 A
Power Dissipation.....	100 mW
Derate from 25°C .....	1.33 mW/ $^{\circ}$ C

### Detector

#### Peak Off-State Voltage

IL420 .....	600 V
IL4208 .....	800 V
RMS On-State Current.....	300 mA
Single Cycle Surge Current.....	3.0 A
Total Power Dissipation .....	500 mW
Derate from 25°C .....	6.6 mW/ $^{\circ}$ C

### Package

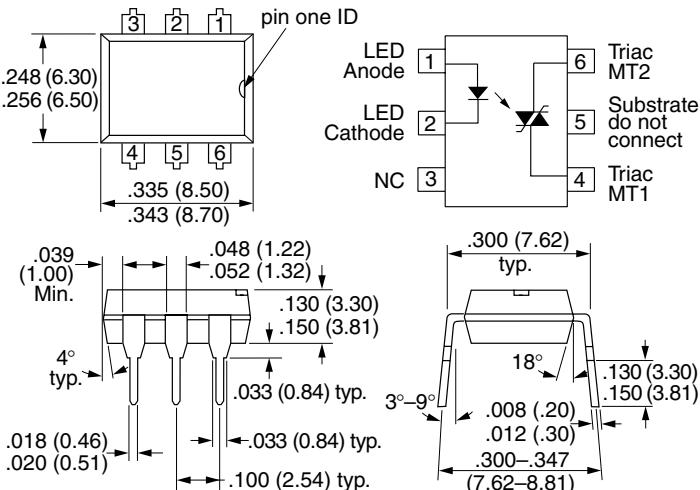
#### Isolation Test Voltage (between emitter

and detector, climate per DIN 50014, part 2, Nov. 74, t=1.0 sec.) .....	5300 V <sub>RMS</sub>
Pollution Degree (DIN VDE 0109) .....	2
Creepage Distance .....	$\geq$ 7.0 mm
Clearance .....	$\geq$ 7.0 mm
Comparative Tracking Index per DIN IEC 112/VDE 0303 part 1, Group IIIa per DIN VDE 6110.....	$\geq$ 175

#### Isolation Resistance

$V_{IO}=500$ V, $T_A=25^{\circ}$ C .....	$\geq 10^{12}$ $\Omega$
$V_{IO}=500$ V, $T_A=100^{\circ}$ C .....	$\geq 10^{11}$ $\Omega$
Storage Temperature Range .....	-55°C to +150°C
Ambient Temperature Range .....	-55°C to +100°C
Soldering Temperature (max. $\leq$ 10 sec.dip soldering $\geq$ 0.5 mm from case bottom).....	260°C

Dimensions in inches (mm)



## DESCRIPTION

The IL420/4208 consists of a GaAs IRLED optically coupled to a photo-sensitive non-zero crossing TRIAC network. The TRIAC consists of two inverse parallel connected monolithic SCRs. These three semiconductors are assembled in a six pin 0.3 inch dual in-line package, using high insulation double molded, over/under leadframe construction.

High input sensitivity is achieved by using an emitter follower phototransistor and a cascaded SCR predriver resulting in an LED trigger current of less than 2.0 mA (DC).

The IL420/4208 uses two discrete SCRs resulting in a commutating dv/dt of greater than 10 kV/ $\mu$ s. The use of a proprietary dv/dt clamp results in a static dv/dt of greater than 10 kV/ $\mu$ s. This clamp circuit has a MOSFET that is enhanced when high dv/dt spikes occur between MT1 and MT2 of the TRIAC. When conducting, the FET clamps the base of the phototransistor, disabling the first stage SCR predriver.

The 600/800 V blocking voltage permits control of off-line voltages up to 240 VAC, with a safety factor of more than two, and is sufficient for as much as 380 VAC.

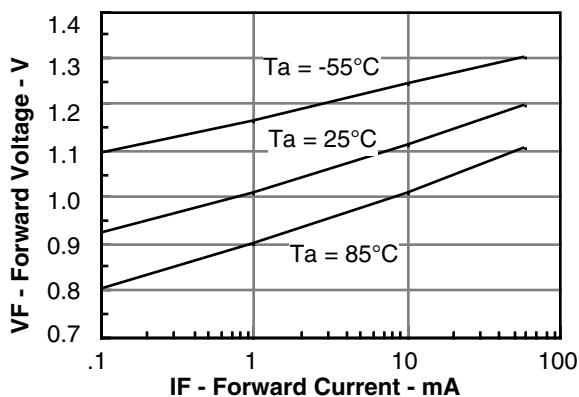
The IL420/4208 isolates low-voltage logic from 120, 240, and 380 VAC lines to control resistive, inductive, or capacitive loads including motors, solenoids, high current thyristors or TRIAC and relays.

Applications include solid-state relays, industrial controls, office equipment, and consumer appliances.

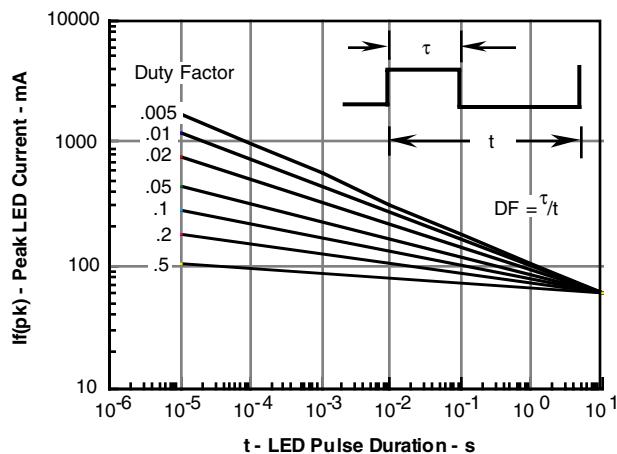
**Characteristics**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
<b>Emitter</b>						
Forward Voltage	$V_F$	—	1.16	1.35	V	$I_F=10 \text{ mA}$
Reverse Current	$I_R$	—	0.1	10	$\mu\text{A}$	$V_R=6.0 \text{ V}$
Capacitance	$C_O$	—	40	—	pF	$V_F=0 \text{ V}, f=1.0 \text{ MHz}$
Thermal Resistance, Junction to Ambient	$R_{THJA}$	—	750	—	K/W	—
<b>Detector</b>						
Off-State Voltage	IL420	$V_D(\text{RMS})$	424	460	—	$I_D(\text{RMS})=70 \mu\text{A}$
	IL4208		565	—	—	
Repetitive Peak Off-State Voltage	IL420	$V_{DRM}$	600	—	—	$I_{DRM}=100 \mu\text{s}$
	IL4208		800	—	—	
Off-State Current	$I_D(\text{RMS})$	—	10	100	$\mu\text{A}$	$V_D=V_{DRM}, T_A=100^\circ\text{C}$
On-State Voltage	$V_{TM}$	—	1.7	3.0	V	$I_T=300 \text{ mA}$
On-State Current	$I_{TM}$	—	—	300	mA	$PF=1.0, V_{T(\text{RMS})}=1.7 \text{ V}$
Surge (Non-Repetitive) On-State Current	$I_{TSM}$	—	—	3.0	A	$f=50 \text{ Hz}$
Holding Current	$I_H$	—	65	500	$\mu\text{A}$	—
Latching Current	$I_L$	—	5.0	—	mA	$V_T=2.2 \text{ V}$
LED Trigger Current	$I_{FT}$	—	1.0	2.0		$V_{AK}=5.0 \text{ V}$
Trigger Current Temperature Gradient	$\Delta I_{FT}/\Delta T_j$	—	7.0	14	$\mu\text{A/K}$	—
Turn-On Time	$t_{ON}$	—	35	—	$\mu\text{s}$	$V_{RM}=V_{DM}=V_D(\text{RMS})$
Turn-Off Time	$t_{OFF}$	—	50	—		$PF=1.0, I_T=300 \text{ mA}$
Critical State of Rise of Off-State Voltage	$dv/dt_{cr}$	10000	—	—	$V/\mu\text{s}$	$V_D=0.67 V_{DRM}, T_j=25^\circ\text{C}$
		5000	—	—		$V_D=0.67 V_{DRM}, T_j=80^\circ\text{C}$
Critical Rate of Rise of Voltage at Current Commutation	$dv/dt_{crq}$	10000	—	—		$V_D=0.67 V_{DRM}, di/dt_{crq} \leq 15 \text{ A/ms}$ $T_j=25^\circ\text{C}$
		5000	—	—		$V_D=0.67 V_{DRM}, di/dt_{crq} \leq 15 \text{ A/ms}$ $T_j=80^\circ\text{C}$
Critical State of Rise of On-State Current	$di/dt_{cr}$	8.0	—	—	A/ $\mu\text{s}$	—
Thermal Resistance, Junction to Ambient	$R_{THJA}$	—	150	—	K/W	—
<b>Package</b>						
Critical Rate of Rise of Coupled Input/Output Voltage	$dv_{(IO)}/dt$	—	5000	—	V/ $\mu\text{s}$	$I_T=0 \text{ A}, V_{RM}=V_{DM}=V_D(\text{RMS})$
Package Capacitance	$C_{IO}$	—	0.8	—	pF	$f=1.0 \text{ MHz}, V_{IO}=0 \text{ V}$
Common Mode Coupling Capacitance	$C_{CM}$	—	0.01	—	pF	—
Isolation Resistance	$R_{IS}$	—	$\geq 10^{12}$	—	$\Omega$	$V_{IO}=500, T_A=25^\circ\text{C}$
		—	$\geq 10^{11}$	—		$V_{IO}=500, T_A=100^\circ\text{C}$

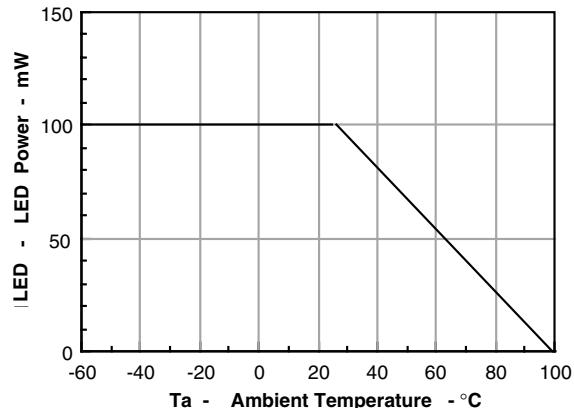
**Figure 1. Forward voltage versus forward current**



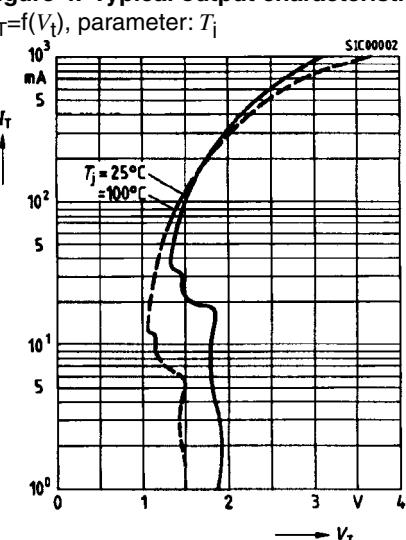
**Figure 2. Peak LED current versus duty factor, Tau**



**Figure 3. Maximum LED power dissipation**

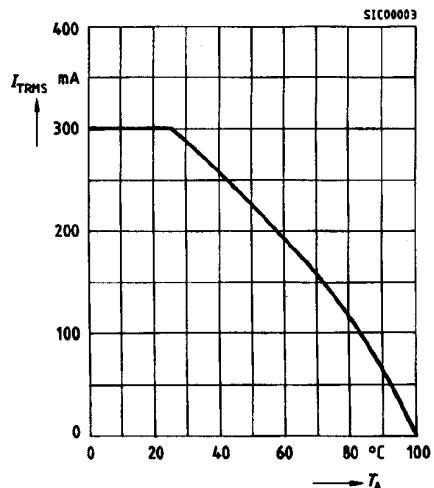


**Figure 4. Typical output characteristics**



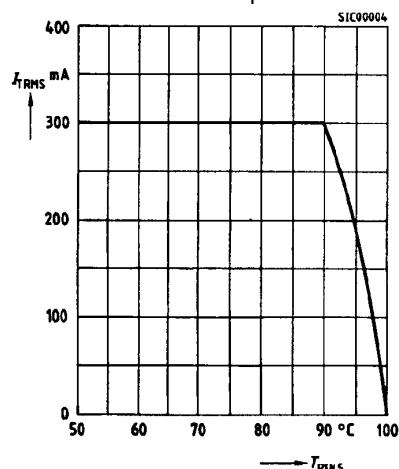
**Figure 5. Current reduction**

$I_{TRMS} = f(T_A)$   $R_{thJA} = 150 \text{ K/W}$   
Device switch is soldered in PCB or base plate



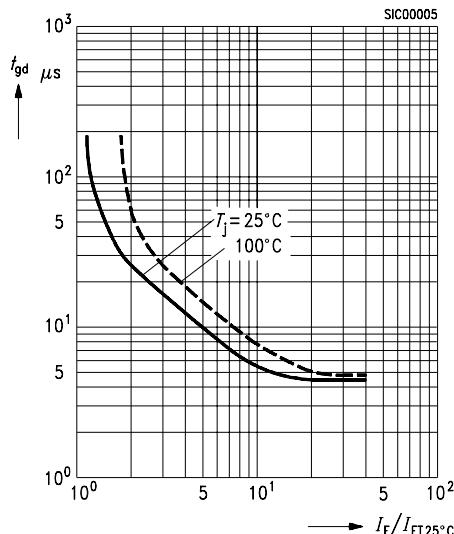
**Figure 6. Current reduction**

$I_{TRMS} = f(T_{PIN5})$ ,  $R_{thJ} = 16.5 \text{ K/W}$   
Thermocouple measurement must be performed potentially separated to A1 and A2. Measuring junction to be as near as possible at case.



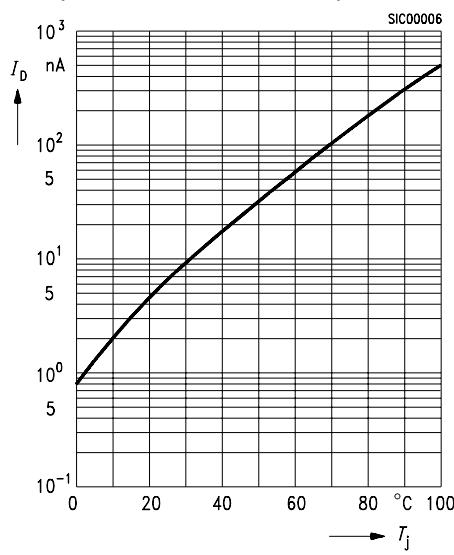
**Figure 7. Typical trigger delay time**

$t_{gd} = f(I_F/I_{FT25^\circ\text{C}})$ ,  $V_D=200$  V, parameter:  $T_j$



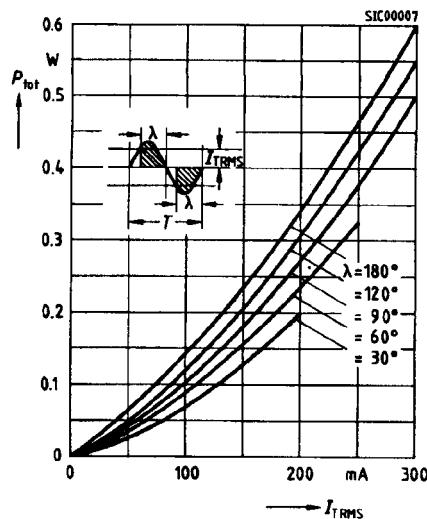
**Figure 8. Typical off-state current**

$I_D = f(T_j)$ ,  $V_D=600$  V, parameter:  $T_j$



**Figure 9. Power dissipation**

$P_{tot} = f(I_{TRMS})$  for 40 to 60 Hz line operation



**Figure 10. Pulse trigger current**

$I_{FTN} = f(t_{pIF})$   $I_{FTN}$  normalized to  $I_{FT}$ , referring to  $t_{pIF} \geq 1.0$  ms,  $V_{OP}=200$  V,  $f=40$  to  $60$  Hz typ.

